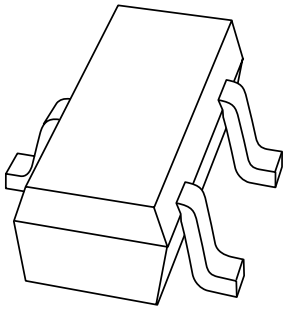
DATA SHEET



BFQ67T
NPN 8 GHz wideband transistor

Preliminary specification

1999 Oct 18

Philips
Semiconductors

PHILIPS

NPN 8 GHz wideband transistor BFQ67T

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability
- SOT416 (SC75) envelope.

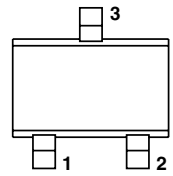
DESCRIPTION

NPN transistor in a plastic SOT416 (SC75) envelope.

It is designed for wideband applications such as satellite TV tuners and RF portable communications equipment up to 2 GHz.

PINNING

PIN	DESCRIPTION
Code: V2	
1	base
2	emitter
3	collector



Top view MBC870

Fig.1 SOT416.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	10	V
I_C	DC collector current		–	–	50	mA
P_{tot}	total power dissipation	up to T_s = 118 °C; note 1	–	–	300	mW
h_{FE}	DC current gain	I_C = 15 mA; V_{CE} = 5 V; T_j = 25 °C	60	100	–	
f_T	transition frequency	I_C = 15 mA; V_{CE} = 8 V; f = 2 GHz; T_{amb} = 25 °C	–	8	–	GHz
G_{UM}	maximum unilateral power gain	I_c = 15 mA; V_{CE} = 8 V; f = 1 GHz; T_{amb} = 25 °C	–	13	–	dB
F	noise figure	I_c = 5 mA; V_{CE} = 8 V; f = 1 GHz	–	1.3	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	10	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	DC collector current		–	50	mA
P_{tot}	total power dissipation	up to T_s = 118 °C; note 1	–	300	mW
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	175	°C

Note

1. T_s is the temperature at the soldering point of the collector tab.

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	up to T_s = 118 °C; note 1	190 K/W

Note

1. T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

T_j = 25 °C, unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 5 V	–	–	50	nA
h_{FE}	DC current gain	I_C = 15 mA; V_{CE} = 5 V	60	100	–	
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = 8 V; f = 1 MHz	–	0.7	–	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = 0.5 V; f = 1 MHz	–	1.3	–	pF
C_{re}	feedback capacitance	I_C = 0; V_{CB} = 8 V; f = 1 MHz	–	0.5	–	pF
f_T	transition frequency	I_C = 15 mA; V_{CE} = 8 V; f = 2 GHz; T_{amb} = 25 °C	–	8	–	GHz
G_{UM}	maximum unilateral power gain (note 1)	I_C = 15 mA; V_{CE} = 8 V; f = 1 GHz T_{amb} = 25 °C	–	13	–	dB
		I_C = 15 mA; V_{CE} = 8 V; f = 2 GHz; T_{amb} = 25 °C	–	8	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; I_C = 5 mA; V_{CE} = 8 V; f = 1 GHz	–	1.3	–	dB
		$\Gamma_s = \Gamma_{opt}$; I_C = 15 mA; V_{CE} = 8 V; f = 1 GHz	–	2	–	dB
		$\Gamma_s = \Gamma_{opt}$; I_C = 5 mA; V_{CE} = 8 V; f = 2 GHz	–	2.2	–	dB
		I_C = 5 mA; V_{CE} = 8 V; f = 2 GHz; Z_s = 60 Ω	–	2.5	–	dB
		$\Gamma_s = \Gamma_{opt}$; I_C = 15 mA; V_{CE} = 8 V; f = 2 GHz	–	2.7	–	dB
		I_C = 5 mA; V_{CE} = 8 V; f = 2 GHz; Z_s = 60 Ω	–	3	–	dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1-|S_{11}|^2)(1-|S_{22}|^2)} \text{ dB.}$$

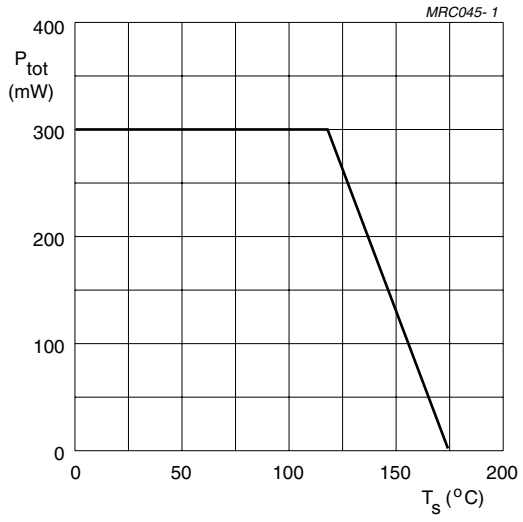
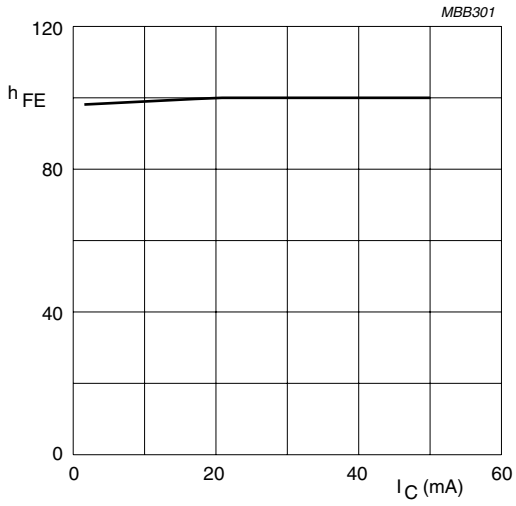
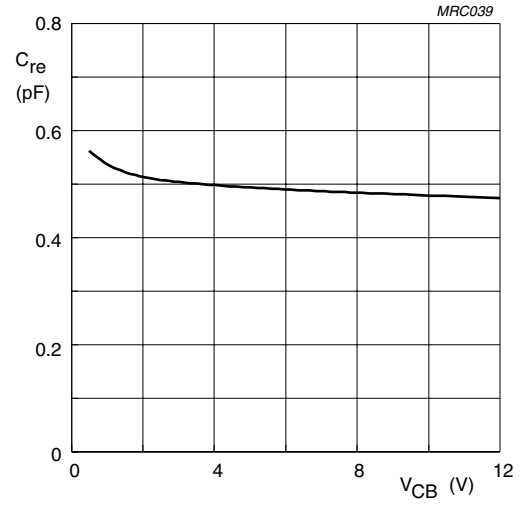


Fig.2 Power derating curve.



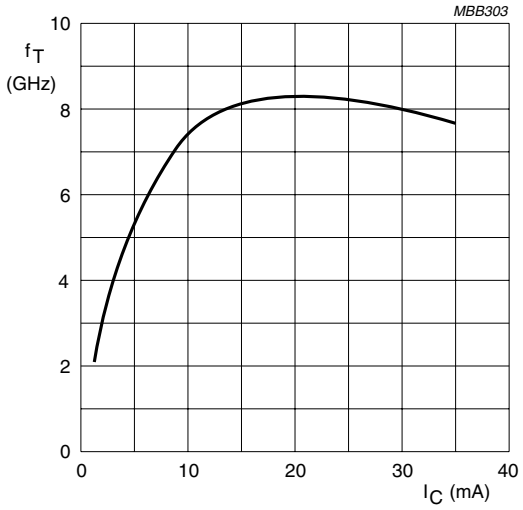
V_{CE} = 5 V; T_j = 25 °C.

Fig.3 DC current gain as a function of collector current.



I_C = 0; f = 1 MHz.

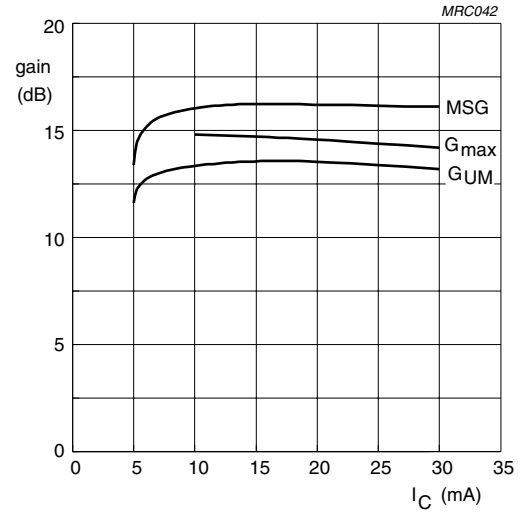
Fig.4 Feedback capacitance as a function of collector-base voltage.



V_{CE} = 8 V; f = 2 GHz; T_{amb} = 25 °C.

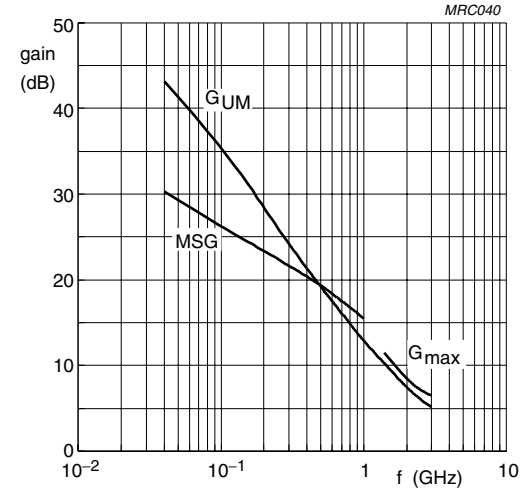
Fig.5 Transition frequency as a function of collector current.

In Figs 6 to 9, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain; G_{max} = maximum available gain.



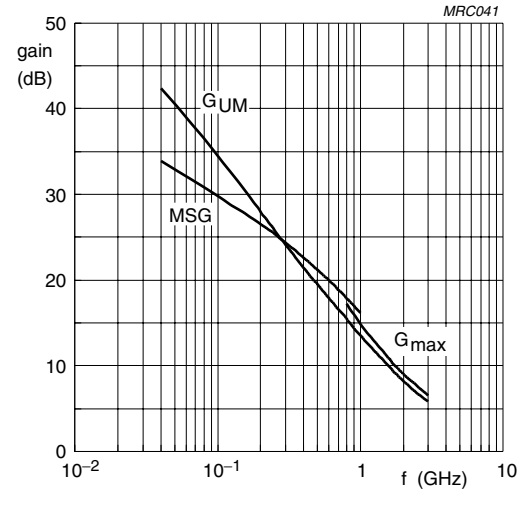
V_{CE} = 8 V; f = 1 GHz; T_{amb} = 25 °C.

Fig.6 Gain as a function of collector current.



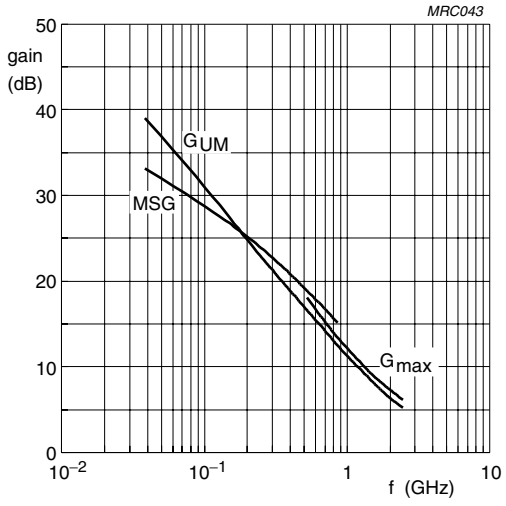
I_C = 5 mA; V_{CE} = 8 V; T_{amb} = 25 °C.

Fig.7 Gain as a function of frequency.



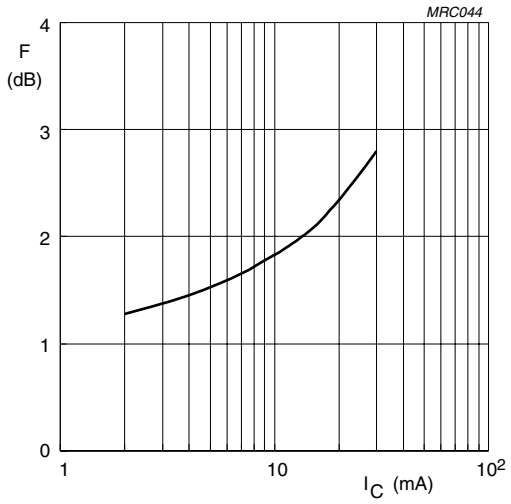
I_C = 15 mA; V_{CE} = 8 V; T_{amb} = 25 °C.

Fig.8 Gain as a function of frequency.



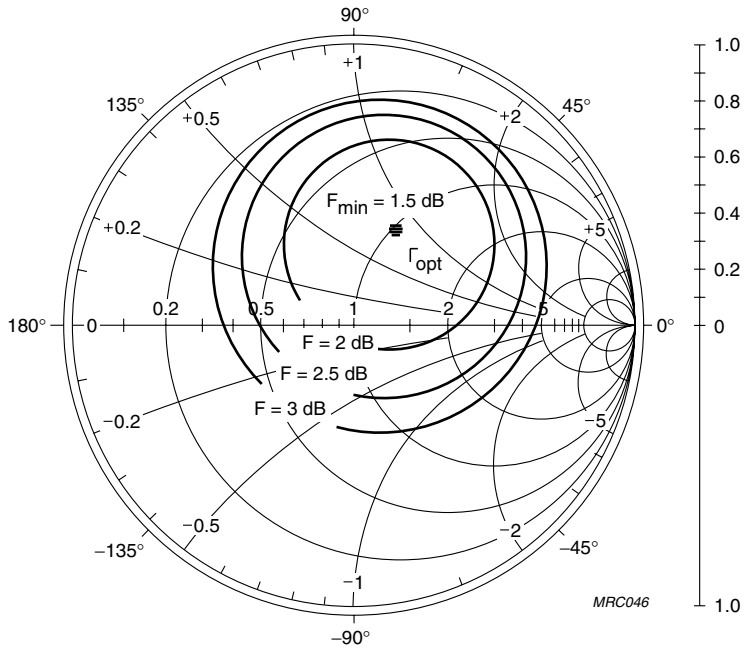
I_C = 30 mA; V_{CE} = 8 V; T_{amb} = 25 °C.

Fig.9 Gain as a function of frequency.



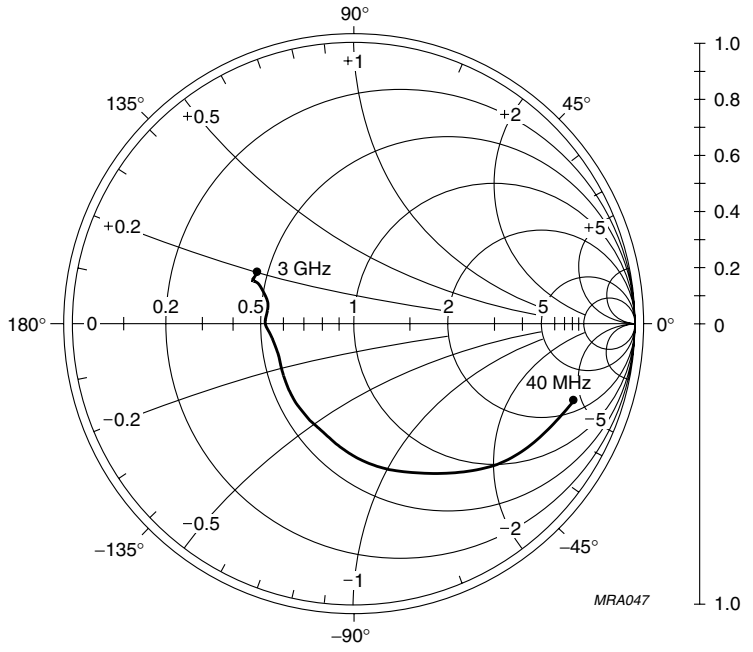
V_{CE} = 8 V; f = 1 GHz.

Fig.10 Minimum noise figure as a function of collector current.



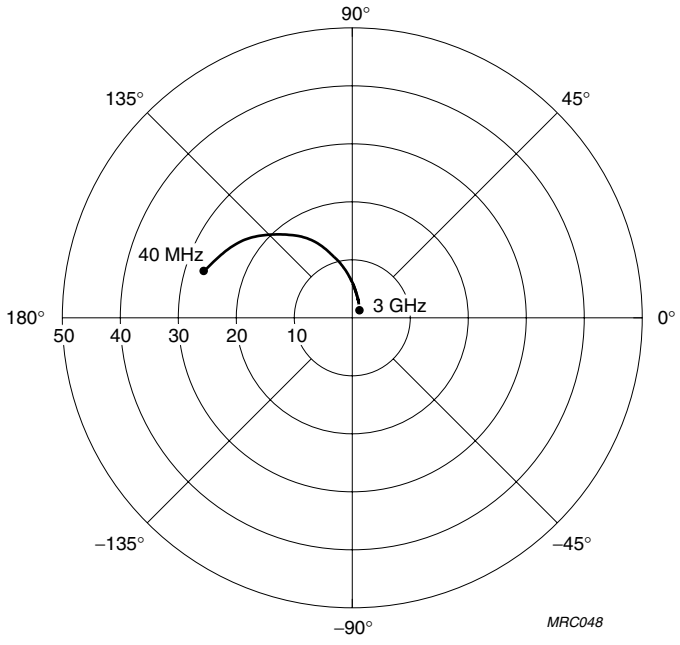
I_C = 5 mA; V_{CE} = 8 V;
f = 1 GHz; Z_o = 50 Ω.

Fig.11 Noise circle.



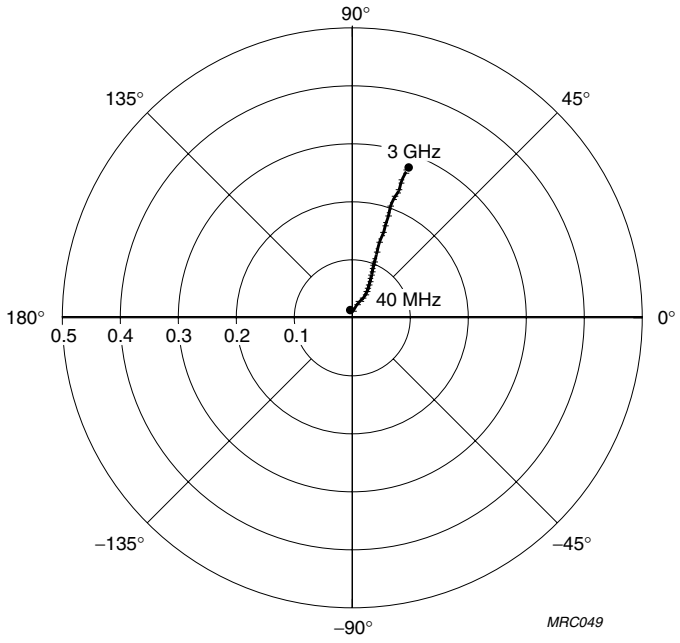
I_C = 15 mA; V_{CE} = 8 V; Z_o = 50 Ω.

Fig.12 Common emitter input reflection coefficient (S_{11}).



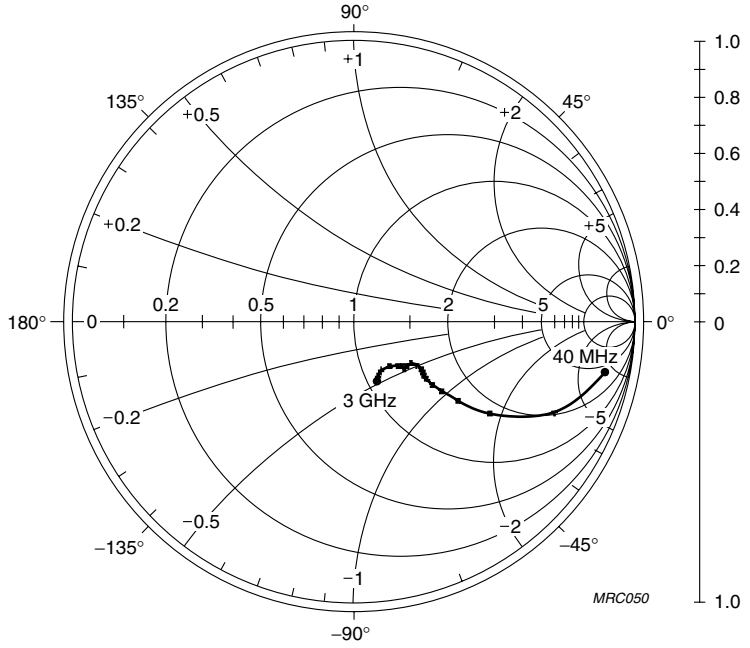
I_C = 15 mA; V_{CE} = 8 V.

Fig.13 Common emitter forward transmission coefficient (S_{21}).



I_C = 15 mA; V_{CE} = 8 V.

Fig.14 Common emitter reverse transmission coefficient (S_{12}).

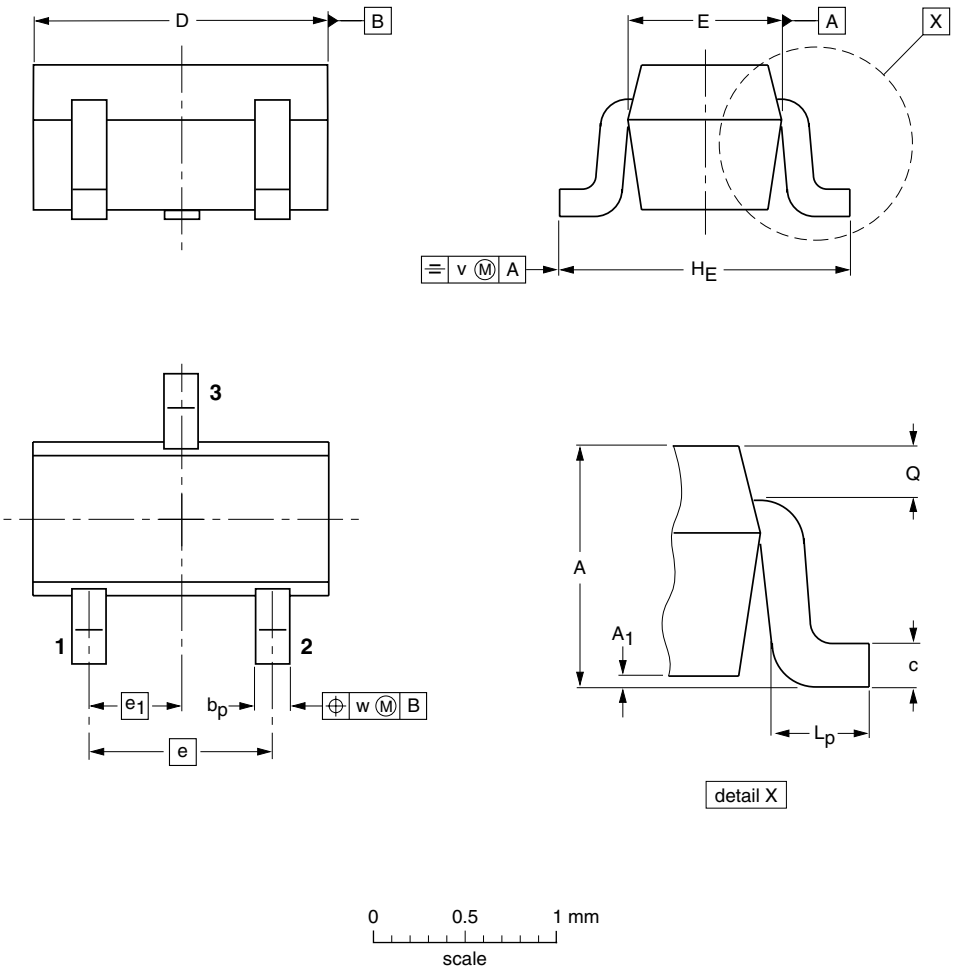


I_C = 15 mA; V_{CE} = 8 V; Z_o = 50 Ω.

Fig.15 Common emitter output reflection coefficient (S_{22}).

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT416**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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